

# 74HC2G32; 74HCT2G32

Dual 2-input OR gate

Rev. 03 — 12 May 2009

Product data sheet

## 1. General description

The 74HC2G32 and 74HCT2G32 are high-speed Si-gate CMOS devices. They provide two 2-input OR gates.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

## 2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

| Type number               | Package   |        |   |          |
|---------------------------|---|--------|---|----------|
|                           | Temperature range   | Name   | Description   | Version  |
| 74HC2G32DP<br>74HCT2G32DP | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | TSSOP8 | plastic thin shrink small outline package; 8 leads;<br>body width 3 mm; lead length 0.5 mm                          | SOT505-2 |
| 74HC2G32DC<br>74HCT2G32DC | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | VSSOP8 | plastic very thin shrink small outline package; 8 leads;<br>body width 2.3 mm                                       | SOT765-1 |
| 74HC2G32GD<br>74HCT2G32GD | $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ | XSON8U | plastic extremely thin small outline package; no leads;<br>8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm | SOT996-2 |

## 4. Marking

Table 2. Marking code

| Type number | Marking code |
|-------------|--------------|
| 74HC2G32DP  | H32          |
| 74HCT2G32DP | T32          |
| 74HC2G32DC  | H32          |
| 74HCT2G32DC | T32          |
| 74HC2G32GD  | H32          |
| 74HCT2G32GD | T32          |

## 5. Functional diagram

**Fig 1. Logic symbol**

**Fig 2. IEC logic symbol**

**Fig 3. Logic diagram (one gate)**

## 6. Pinning information

### 6.1 Pinning

**74HC2G32  
74HCT2G32**

**74HC2G32  
74HCT2G32**

Transparent top view

**Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)**

**Fig 5. Pin configuration SOT996-2 (XSON8U)**

## 6.2 Pin description

**Table 3.** Pin description

| Symbol          | Pin  | Description    |
|-----------------|------|----------------|
| 1A, 2A          | 1, 5 | data input     |
| 1B, 2B          | 2, 6 | data input     |
| GND             | 4    | ground (0 V)   |
| 1Y, 2Y          | 7, 3 | data output    |
| V <sub>CC</sub> | 8    | supply voltage |

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

| Input |    | Output |
|-------|----|--------|
| nA    | nB | nY     |
| L     | L  | L      |
| L     | H  | H      |
| H     | L  | H      |
| H     | H  | H      |

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol           | Parameter                 | Conditions   | Min     | Max  | Unit |
|------------------|---------------------------|--|---------|------|------|
| V <sub>CC</sub>  | supply voltage            |  | -0.5    | +7.0 | V    |
| I <sub>IK</sub>  | input clamping current    | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ | [1] -   | ±20  | mA   |
| I <sub>OK</sub>  | output clamping current   | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ | [1] -   | ±20  | mA   |
| I <sub>O</sub>   | output current            | $V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$     | [1] -   | 25   | mA   |
| I <sub>CC</sub>  | supply current            |  | [1] -   | 50   | mA   |
| I <sub>GND</sub> | ground current            |  | [1] -50 | -    | mA   |
| T <sub>stg</sub> | storage temperature       |  | -65     | +150 | °C   |
| P <sub>D</sub>   | dynamic power dissipation | T <sub>amb</sub> = -40 °C to +125 °C                   | [2] -   | 300  | mW   |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.  
 For XSON8U package: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

| Symbol           | Parameter                           | Conditions              | 74HC2G32 |      |                 | 74HCT2G32 |      |                 | Unit |
|------------------|-------------------------------------|-------------------------|----------|------|-----------------|-----------|------|-----------------|------|
|                  |                                     |                         | Min      | Typ  | Max             | Min       | Typ  | Max             |      |
| V <sub>CC</sub>  | supply voltage                      |                         | 2.0      | 5.0  | 6.0             | 4.5       | 5.0  | 5.5             | V    |
| V <sub>I</sub>   | input voltage                       |                         | 0        | -    | V <sub>CC</sub> | 0         | -    | V <sub>CC</sub> | V    |
| V <sub>O</sub>   | output voltage                      |                         | 0        | -    | V <sub>CC</sub> | 0         | -    | V <sub>CC</sub> | V    |
| T <sub>amb</sub> | ambient temperature                 |                         | -40      | +25  | +125            | -40       | +25  | +125            | °C   |
| Δt/ΔV            | input transition rise and fall rate | V <sub>CC</sub> = 2.0 V | -        | -    | 625             | -         | -    | -               | ns/V |
|                  |                                     | V <sub>CC</sub> = 4.5 V | -        | 1.67 | 139             | -         | 1.67 | 139             | ns/V |
|                  |                                     | V <sub>CC</sub> = 6.0 V | -        | -    | 83              | -         | -    | -               | ns/V |

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

| Symbol          | Parameter                 | Conditions   | 25 °C |      |      | -40 °C to +85 °C |      | -40 °C to +125 °C |      | Unit |
|-----------------|---------------------------|--|-------|------|------|------------------|------|-------------------|------|------|
|                 |                           |  | Min   | Typ  | Max  | Min              | Max  | Min               | Max  |      |
| <b>74HC2G32</b> |                           |  |       |      |      |                  |      |                   |      |      |
| V <sub>IH</sub> | HIGH-level input voltage  | V <sub>CC</sub> = 2.0 V  | 1.5   | 1.2  | -    | 1.5              | -    | 1.5               | -    | V    |
|                 |                           | V <sub>CC</sub> = 4.5 V  | 3.15  | 2.4  | -    | 3.15             | -    | 3.15              | -    | V    |
|                 |                           | V <sub>CC</sub> = 6.0 V  | 4.2   | 3.2  | -    | 4.2              | -    | 4.2               | -    | V    |
| V <sub>IL</sub> | LOW-level input voltage   | V <sub>CC</sub> = 2.0 V  | -     | 0.8  | 0.5  | -                | 0.5  | -                 | 0.5  | V    |
|                 |                           | V <sub>CC</sub> = 4.5 V  | -     | 2.1  | 1.35 | -                | 1.35 | -                 | 1.35 | V    |
|                 |                           | V <sub>CC</sub> = 6.0 V  | -     | 2.8  | 1.8  | -                | 1.8  | -                 | 1.8  | V    |
| V <sub>OH</sub> | HIGH-level output voltage | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>                                    |       |      |      |                  |      |                   |      |      |
|                 |                           | I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V                                       | 1.9   | 2.0  | -    | 1.9              | -    | 1.9               | -    | V    |
|                 |                           | I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V                                       | 4.4   | 4.5  | -    | 4.4              | -    | 4.4               | -    | V    |
|                 |                           | I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V                                       | 5.9   | 6.0  | -    | 5.9              | -    | 5.9               | -    | V    |
|                 |                           | I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V                                      | 4.18  | 4.32 | -    | 4.13             | -    | 3.7               | -    | V    |
| V <sub>OL</sub> | LOW-level output voltage  | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>                                    |       |      |      |                  |      |                   |      |      |
|                 |                           | I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V  | -     | 0    | 0.1  | -                | 0.1  | -                 | 0.1  | V    |
|                 |                           | I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V  | -     | 0    | 0.1  | -                | 0.1  | -                 | 0.1  | V    |
|                 |                           | I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V  | -     | 0    | 0.1  | -                | 0.1  | -                 | 0.1  | V    |
|                 |                           | I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V                                       | -     | 0.15 | 0.26 | -                | 0.33 | -                 | 0.4  | V    |
| I <sub>I</sub>  | input leakage current     | V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V                       | -     | -    | ±0.1 | -                | ±1.0 | -                 | ±1.0 | μA   |
|                 |                           | V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V | -     | -    | 1.0  | -                | 10   | -                 | 20   | μA   |

**Table 7. Static characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V).

| Symbol           | Parameter                 | Conditions  | 25 °C |      |      | -40 °C to +85 °C |      | -40 °C to +125 °C |      | Unit |
|------------------|---------------------------|---|-------|------|------|------------------|------|-------------------|------|------|
|                  |                           |   | Min   | Typ  | Max  | Min              | Max  | Min               | Max  |      |
| C <sub>I</sub>   | input capacitance         |   | -     | 1.5  | -    | -                | -    | -                 | -    | pF   |
| <b>74HCT2G32</b> |                           |   |       |      |      |                  |      |                   |      |      |
| V <sub>IH</sub>  | HIGH-level input voltage  | V <sub>CC</sub> = 4.5 V to 5.5 V  | 2.0   | 1.6  | -    | 2.0              | -    | 2.0               | -    | V    |
| V <sub>IL</sub>  | LOW-level input voltage   | V <sub>CC</sub> = 4.5 V to 5.5 V  | -     | 1.2  | 0.8  | -                | 0.8  | -                 | 0.8  | V    |
| V <sub>OH</sub>  | HIGH-level output voltage | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V                               |       |      |      |                  |      |                   |      |      |
|                  |                           | I <sub>O</sub> = -20 µA   | 4.4   | 4.5  | -    | 4.4              | -    | 4.4               | -    | V    |
|                  |                           | I <sub>O</sub> = -4.0 mA  | 4.18  | 4.32 | -    | 4.13             | -    | 3.7               | -    | V    |
| V <sub>OL</sub>  | LOW-level output voltage  | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V                               |       |      |      |                  |      |                   |      |      |
|                  |                           | I <sub>O</sub> = 20 µA  | -     | 0    | 0.1  | -                | 0.1  | -                 | 0.1  | V    |
|                  |                           | I <sub>O</sub> = 4.0 mA   | -     | 0.15 | 0.26 | -                | 0.33 | -                 | 0.4  | V    |
| I <sub>I</sub>   | input leakage current     | V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V  | -     | -    | ±0.1 | -                | ±1.0 | -                 | ±1.0 | µA   |
| I <sub>CC</sub>  | supply current            | V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V                      | -     | -    | 1.0  | -                | 10   | -                 | 20   | µA   |
| ΔI <sub>CC</sub> | additional supply current | per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A | -     | -    | 300  | -                | 375  | -                 | 410  | µA   |
| C <sub>I</sub>   | input capacitance         |   | -     | 1.5  | -    | -                | -    | -                 | -    | pF   |

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

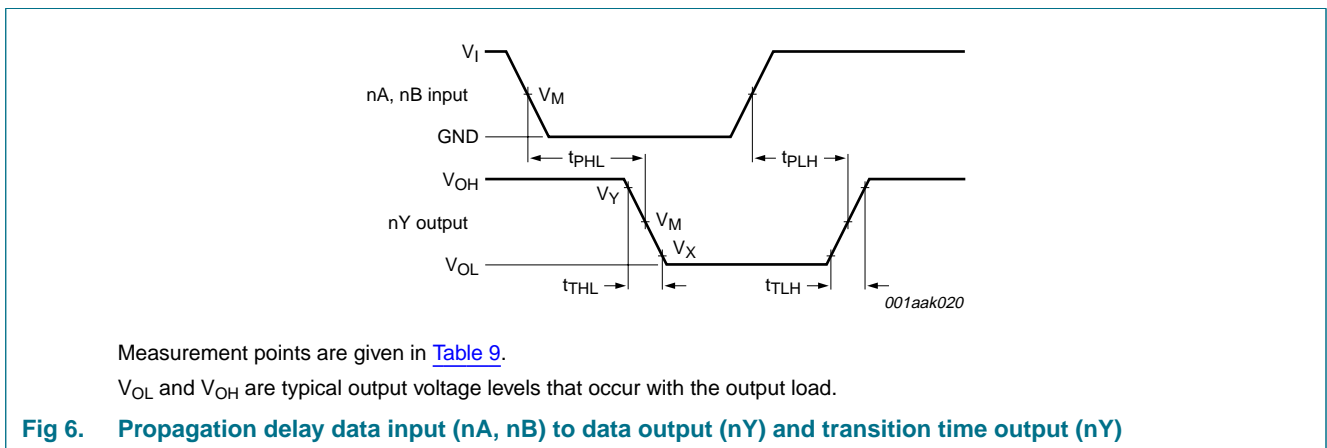
| Symbol          | Parameter                     | Conditions  | 25 °C |     |     | -40 °C to +85 °C |     | -40 °C to +125 °C |     | Unit |
|-----------------|-------------------------------|---|-------|-----|-----|------------------|-----|-------------------|-----|------|
|                 |                               |   | Min   | Typ | Max | Min              | Max | Min               | Max |      |
| <b>74HC2G32</b> |                               |   |       |     |     |                  |     |                   |     |      |
| t <sub>pd</sub> | propagation delay             | nA, nB to nY; see <a href="#">Figure 6</a> [1]  |       |     |     |                  |     |                   |     |      |
|                 |                               | V <sub>CC</sub> = 2.0 V   | -     | 24  | 75  | -                | 95  | -                 | 110 | ns   |
|                 |                               | V <sub>CC</sub> = 4.5 V   | -     | 9.0 | 15  | -                | 19  | -                 | 22  | ns   |
|                 |                               | V <sub>CC</sub> = 6.0 V   | -     | 7.0 | 13  | -                | 16  | -                 | 20  | ns   |
| t <sub>t</sub>  | transition time               | nY; see <a href="#">Figure 6</a> [2]  |       |     |     |                  |     |                   |     |      |
|                 |                               | V <sub>CC</sub> = 2.0 V   | -     | 18  | 75  | -                | 95  | -                 | 125 | ns   |
|                 |                               | V <sub>CC</sub> = 4.5 V   | -     | 6   | 15  | -                | 19  | -                 | 25  | ns   |
|                 |                               | V <sub>CC</sub> = 6.0 V   |       | 5   | 13  | -                | 16  | -                 | 20  | ns   |
| C <sub>PD</sub> | power dissipation capacitance | per buffer; C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> | [3]   | -   | 10  | -                | -   | -                 | -   | pF   |

**Table 8. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

| Symbol           | Parameter                     | Conditions  | 25 °C |     |     | -40 °C to +85 °C |     | -40 °C to +125 °C |     | Unit |
|------------------|-------------------------------|---|-------|-----|-----|------------------|-----|-------------------|-----|------|
|                  |                               |   | Min   | Typ | Max | Min              | Max | Min               | Max |      |
| <b>74HCT2G32</b> |                               |   |       |     |     |                  |     |                   |     |      |
| $t_{pd}$         | propagation delay             | nA, nB to nY; see <a href="#">Figure 6</a> [1]<br>$V_{CC} = 4.5\text{ V}$                     | -     | 13  | 24  | -                | 30  | -                 | 36  | ns   |
| $t_t$            | transition time               | nY; see <a href="#">Figure 6</a> [2]<br>$V_{CC} = 4.5\text{ V}$                               | -     | 6   | 15  | -                | 19  | -                 | 22  | ns   |
| $C_{PD}$         | power dissipation capacitance | per buffer;<br>$C_L = 50\text{ pF}$ ; $f_i = 1\text{ MHz}$ ;<br>$V_I = \text{GND to } V_{CC}$ | [3]   | 11  | -   | -                | -   | -                 | -   | pF   |

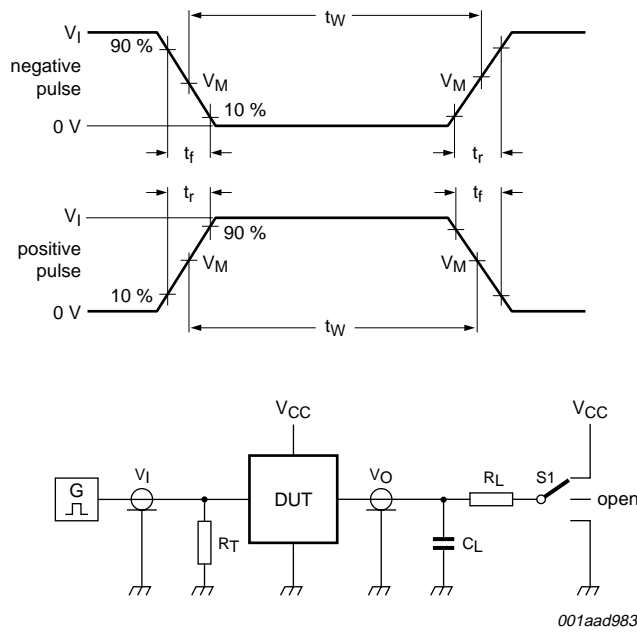
- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $t_t$  is the same as  $t_{TLH}$  and  $t_{THL}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz;  
 $f_o$  = output frequency in MHz;  
 $C_L$  = output load capacitance in pF;  
 $V_{CC}$  = supply voltage in V;  
 $N$  = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 12. Waveforms



**Table 9. Measurement points**

| Type      | Input       | Output      |             |             |
|-----------|-------------|-------------|-------------|-------------|
|           | $V_M$       | $V_M$       | $V_X$       | $V_Y$       |
| 74HC2G32  | $0.5V_{CC}$ | $0.5V_{CC}$ | $0.1V_{CC}$ | $0.9V_{CC}$ |
| 74HCT2G32 | 1.3 V       | 1.3 V       | $0.1V_{CC}$ | $0.9V_{CC}$ |



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 7. Load circuit for measuring switching times**

**Table 10. Test data**

| Type      | Input           |             | Load  |              | S1 position        |
|-----------|-----------------|-------------|-------|--------------|--------------------|
|           | $V_I$           | $t_r, t_f$  | $C_L$ | $R_L$        | $t_{PHL}, t_{PLH}$ |
| 74HC2G32  | GND to $V_{CC}$ | $\leq 6$ ns | 50 pF | 1 k $\Omega$ | open               |
| 74HCT2G32 | GND to 3 V      | $\leq 6$ ns | 50 pF | 1 k $\Omega$ | open               |

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

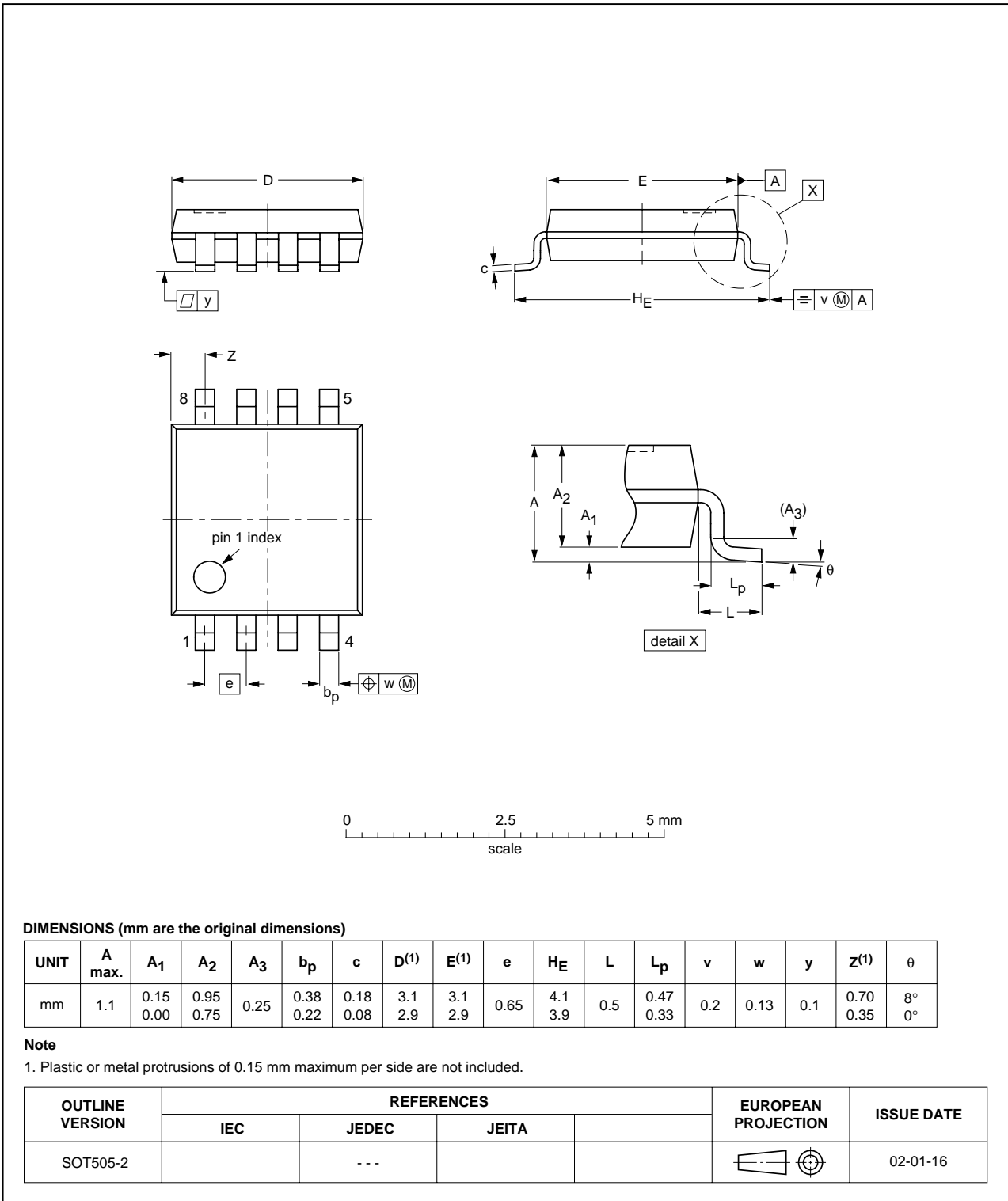


Fig 8. Package outline SOT505-2 (TSSOP8)



VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

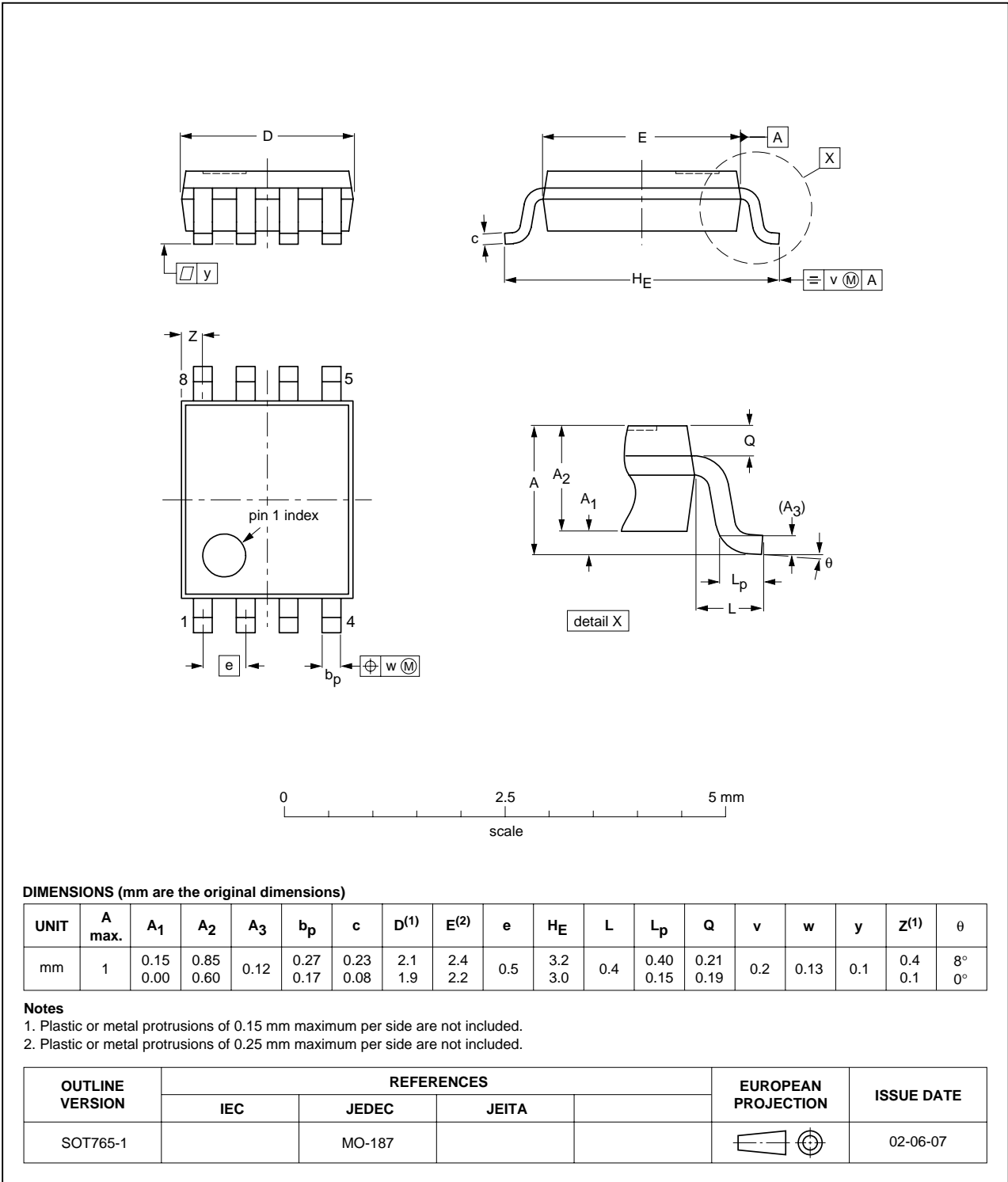


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

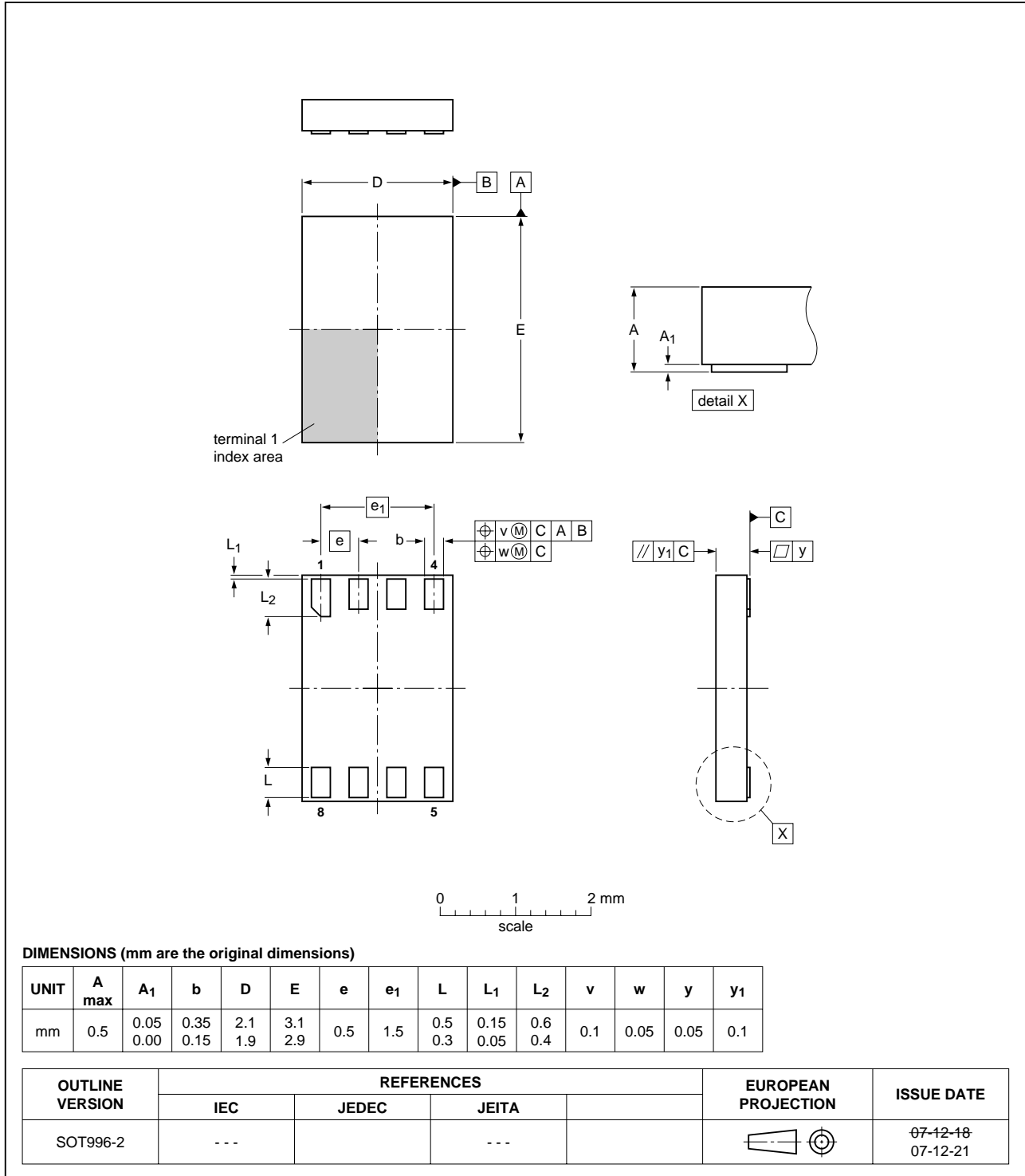


Fig 10. Package outline SOT996-2 (XSON8U)

## 14. Abbreviations

Table 11. Abbreviations

| Acronym | Description                             |
|---------|---|
| CMOS    | Complementary Metal Oxide Semiconductor |
| DUT     | Device Under Test                       |
| ESD     | ElectroStatic Discharge                 |
| HBM     | Human Body Model                        |
| MM      | Machine Model                           |
| TTL     | Transistor-Transistor Logic             |

## 15. Revision history

Table 12. Revision history

| Document ID    | Release date | Data sheet status  | Change notice | Supersedes     |
|----------------|--------------|--|---------------|----------------|
| 74HC_HCT2G32_3 | 20090512     | Product data sheet   | -             | 74HC_HCT2G32_2 |
| Modifications: |              | <ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Added type number 74HC2G32GD and 74HCT2G32GD (XSON8U package)</li></ul> |               |                |
| 74HC_HCT2G32_2 | 20031030     | Product specification  | -             | 74HC_HCT2G32_1 |
| 74HC_HCT2G32_1 | 20020717     | Product specification  | -             | -              |

## 16. Legal information

### 16.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 12 May 2009

Document identifier: 74HC\_HCT2G32\_3